Product Preview

3 A Synchronous Buck Regulator

The NCP3155 is a DC/DC synchronous switching regulator with fully integrated power switches and full fault protection. The switching frequency of 1 MHz and 500 kHz allows the use of small filter components, which results in smaller board space and reduced BOM cost. Available in a SOIC-8 package.

Features

- Input Voltage Range from 4.7 V to 24 V
- Adjustable Output Voltage
- 1 MHz Operation (NCP3155B 500 kHz)
- Internally Programmed 4.1 ms Soft-Start
- 0.8 ± 1.0% Reference Voltage
- $100 \text{ m}\Omega$ HS-FET and $50 \text{ m}\Omega$ LS-FET
- Current Limit and Short Circuit Protection
- Transconductance Amplifier with External Compensation
- Input Undervoltage Lockout
- Output Overvoltage and Undervoltage Detection
- This is a Pb-Free Device

Typical Applications

- Set Top Boxes
- DVD Drives and HDD
- LCD Monitors and TVs
- Cable Modems
- Telecom/Networking/Datacom Equipment

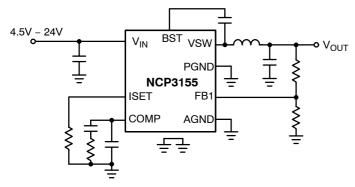


Figure 1. Typical Application Circuit

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.



ON Semiconductor®

http://onsemi.com



SOIC-8 NB CASE 751

MARKING DIAGRAM



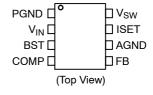
3155x = Specific Device Code

x = A or B

A = Assembly Location

L = Wafer Lot Y = Year W = Work Week ■ Pb-Free Package

PIN CONNECTIONS



ORDERING INFORMATION

Device	Package	Shipping [†]
NCP3155ADR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCP3155BDR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

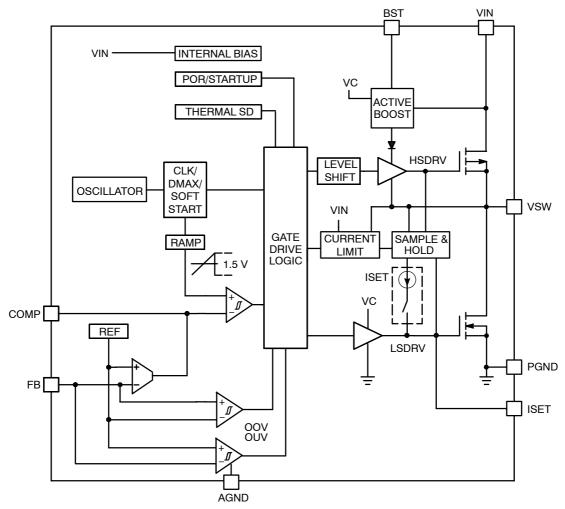


Figure 2. NCP3155 Block Diagram

PIN FUNCTION DESCRIPTION

Pin	Pin Name	Description
1	PGND	The PGND pin is the high current ground pin for the lower MOSFET and drivers which should be soldered to a large copper area to reduce thermal resistance.
2	V _{IN}	The V_{IN} pin powers the internal control circuitry and is monitored by an undervoltage comparator. The V_{IN} pin is also connected to the internal power NMOS switch. It is also used in conjunction with the V_{SW} pin to sense current in the high side MOSFET. The V_{IN} pin has high dl/dt edges and must be decoupled to PGND pin close to the pin of the device.
3	BST	Supply rail for the floating top gate driver. Connect a capacitor (CBST) between this pin and the V _{SW} pin. Typical values for CBST range from 1 nF to 10 nF.
4	COMP	Compensation pin. The comp pin is the output of the transconductance amplifier and the non-inverting input of the PWM comparator. The comp pin in conjunction with the FB pin are used to compensate the voltage-control feedback loop.
5	FB	Inverting input to the Operational Transconductance Amplifier (OTA). The FB pin in conjunction with the external compensation serves to stabilize and achieve the desired output voltage with voltage mode compensation.
6	AGND	The AGND pin serves as small-signal ground. All small-signal ground paths should connect to the AGND pin at a single point to avoid any high current ground returns.
7	ISET	Bottom gate MOSFET driver pin and the internal current set pin. Place a resistor to ground to set the current limit of the converter.
8	V _{SW}	The V_{SW} pin is the connection of the drain and source of the internal N MOSFETS. The V_{SW} pin swings from V_{IN} when the high side switch is on to small negative voltages when the low side switch is on with high dV/dt transitions.

ABSOLUTE MAXIMUM RATINGS (measured vs. GND pin 8, unless otherwise noted)

Rating	Symbol	V _{MAX}	V _{MIN}	Unit
Main Supply Voltage Input	V _{CC}	26.4	-0.3	V
Boost to V _{SW} differential voltage	BST-V _{SW}	13.2	-0.3	V
High Side Drive Boost Pin	BST	45	-0.3	V
Switch Voltage Node	V _{SW}	30	-0.6	V
Transconductance Amplifier Output	COMP	5.5	-0.3	V
Feedback	FB	6.0	-0.3	V
Current Limit Set	ISET	13.2	-0.3	V
Operating Junction Temperature Range (Note 1)	T _J	-40 to +140		°C
Maximum Junction Temperature	$T_{J(MAX)}$	+150		°C
Storage Temperature Range	T _{stg}	-55 to +150		°C
Thermal Characteristics SOIC-8 Plastic Package (Note 2) Maximum Power Dissipation @ T _A = 25°C Thermal Resistance Junction-to-Air Linear Derating Factor	PD R _{θJA}	TBD TBD TBD		W °C/W mW/°C
Lead Temperature Soldering (10 sec): Reflow (SMD styles only) Pb-Free (Note 3)	R_{F}	260 Peak		°C
Moisture Sensitivity Level (Note 4)	MSL	;	3	
ESD Withstand Voltage (Note 5) Human Body Model Machine Model	V _{ESD}	2.0 200		kV V
Latch-up Current (T _A = 85°C) (Note 6)	Lu	+1	00	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

The maximum package power dissipation limit must not be exceeded.

$$P_{D} = \frac{T_{J(max)} - T_{A}}{R_{\theta JA}}$$

- 2. When mounted on minimum recommended FR-4 or G-10 board
- 3. 60-180 seconds minimum above 237°C.
- 4. Moisture Sensitivity Level (MSL): 3 per IPC/JEDEC standard: J-STD-020A.
- This device series contains ESD protection and exceeds the following tests: Human Body Model (HBM) per JEDEC standard: JESD22-A114.
 Machine Model (MM) per JEDEC standard: JESD22-A115.
- 6. Latch-up Current Maximum Rating: per JEDEC standard: JESD78.

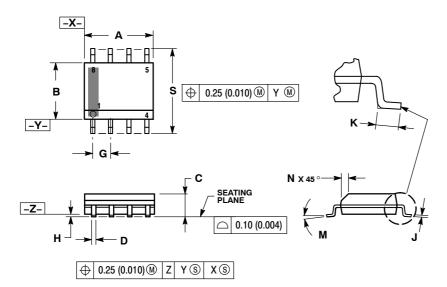
$\textbf{ELECTRICAL CHARACTERISTICS} \ \left(-40^{\circ}\text{C} < \text{T}_{\text{J}} < +125^{\circ}\text{C}, \ \text{V}_{\text{CC}} = 12 \ \text{V}, \ \text{for min/max values unless otherwise noted}\right)$

Characterist	ic	Conditions	Min	Тур	Max	Unit
Input Voltage Range		-	4.7		24	V
SUPPLY CURRENT						
V _{CC} Supply Current	NCP3155A	V_{FB} = 0.55 V, Switching, V_{CC} = 4.7 V	-	TBD	TBD	mA
		V _{FB} = 0.55 V, Switching, V _{CC} = 24 V	-	TBD	TBD	mA
V _{CC} Supply Current	NCP3155B	V_{FB} = 0.55 V, Switching, V_{CC} = 4.7 V	-	TBD	TBD	mA
		V _{FB} = 0.55 V, Switching, V _{CC} = 24 V	-	TBD	TBD	mA
UNDER VOLTAGE LOC	KOUT			•		
UVLO Rising Threshold		V _{CC} Rising Edge	4.0	4.3	4.7	V
UVLO Falling Threshold		V _{CC} Falling Edge	3.5	3.9	4.3	V
OSCILLATOR			1		1	
Oscillator Frequency	NCP3155A	$T_{J} = +25^{\circ}C, 4.7 \text{ V} \le V_{CC} \le 28 \text{ V}$	830	1000	1170	kHz
		$T_J = -40^{\circ}\text{C to } +125^{\circ}\text{C}, 4.7 \text{ V} \le V_{CC} \le 28 \text{ V}$	820	1000	1180	kHz
Oscillator Frequency	NCP3155B	$T_J = +25^{\circ}C, 4.7 \text{ V} \le V_{CC} \le 28 \text{ V}$	415	500	585	kHz
, ,		$T_J = -40^{\circ}\text{C to } +125^{\circ}\text{C}, 4.7 \text{ V} \le \text{V}_{CC} \le 28 \text{ V}$	400	500	600	kHz
Ramp-Amplitude Voltag	е	V _{peak} - V _{alley}	_	1.5	_	V
Ramp Valley Voltage		pour uney	0.46	0.71	0.85	V
PWM	<u>.</u>					
Minimum Duty Cycle		(Note 7)	_	7.0	_	%
Maximum Duty Cycle		,	80	84	_	%
Soft Start Ramp Time	NCP3155A	V _{FB} = V _{COMP}	_	4.1	_	ms
,	NCP3155B	1 B COWN	-	4.1	_	
ERROR AMPLIFIER (G	M)					
Transconductance			0.9	1.3	1.7	mS
Open Loop dc Gain		(Notes 7 and 9)	-	70	-	dB
Output Source Current		V _{FB} = 545 mV	45	70	100	μΑ
Output Sink Current		V _{FB} = 655 mV	45	70	100	μΑ
FB Input Bias Current			-	0.5	500	nA
Feedback Voltage		TJ = 25 C 4.7 V < V _{IN} < 28 V, -40°C < T _J < +125°C	0.792 0.784	0.8 0.8	0.808 0.816	V V
COMP High Voltage		V _{FB} = 0 V	4.0	4.4	5.0	V
COMP Low Voltage		V _{FB} = 2.0 V	-	72	250	mV
OUTPUT VOLTAGE FA	ULTS					
Feedback OOV Thresho	old		0.91	1.00	1.09	V
Feedback OUV Thresho	ıld		0.56	0.60	0.64	V
PWM OUTPUT STAGE	•					
High-Side Switch On Re	esistance	V _{IN} = 12 V V _{IN} = 4.7 V	- -	60 80	75 100	mΩ
Low-Side Switch On Re	esistance	V _{IN} = 12 V V _{IN} = 4.7 V		36 45	40 50	mΩ
OVERCURRENT			1	I.	1	1
ISET Source Current			_	12.5	_	μА
Current Limit Set Voltage (Note 8)		R _{SET} = 22.5 kΩ	_	298	_	mV
THERMAL SHUTDOWN	,	<u>5</u> 2.	1	1	<u>I</u>	1
Thermal Shutdown		(Notes 7 and 10)	_	175	_	°C
Hysteresis		(Notes 7 and 10)	_	20	_	°C
7 Guarantood by docid		(1		<u> </u>	

^{7.} Guaranteed by design.
8. The voltage sensed across the high side MOSFET during conduction.
9. This assumes 100 pF capacitance to ground on the COMP Pin and a typical internal R_0 of > 10 M Ω .
10. This is not a protection feature.

PACKAGE DIMENSIONS

SOIC-8 NB CASE 751-07 ISSUE AJ

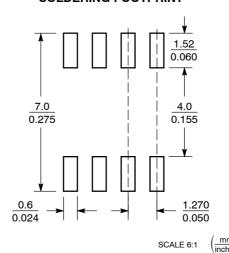


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- MAXIMUM MATERIAL CONDITION.
 6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIN	IETERS	INCHES			
DIM	MIN	MAX	MIN	MAX		
Α	4.80	5.00	0.189	0.197		
В	3.80	4.00	0.150	0.157		
С	1.35	1.75	0.053	0.069		
D	0.33	0.51	0.013	0.020		
G	1.27	1.27 BSC		0.050 BSC		
Н	0.10	0.25	0.004	0.010		
J	0.19	0.25	0.007	0.010		
K	0.40	1.27	0.016	0.050		
M	0 °	8 °	0 °	8		
N	0.25	0.50	0.010	0.020		
S	5.80	6.20	0.228	0.244		

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative